D6-7-660-50



Application

Medical

Industrial optical Sensor

Property

Wavelength λ = 660 nm

Output Power = 50mW

Package Type = φ 5.6mm

Introduction

Egismos currently markets AlGaInP based red laser diodes in the 635nm~ 670nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications.

Laser Diode Key features

Absolute Maximum Rating at Tc=25℃

Items		Symbols	Values	Unit
Operating Current power		P_o	50	mW
Reverse Voltage	LD	V_R	2	V
Operating Temperature		T_{case}	-10~+70	℃
Storage Temperature		T_s	-40~+85	℃

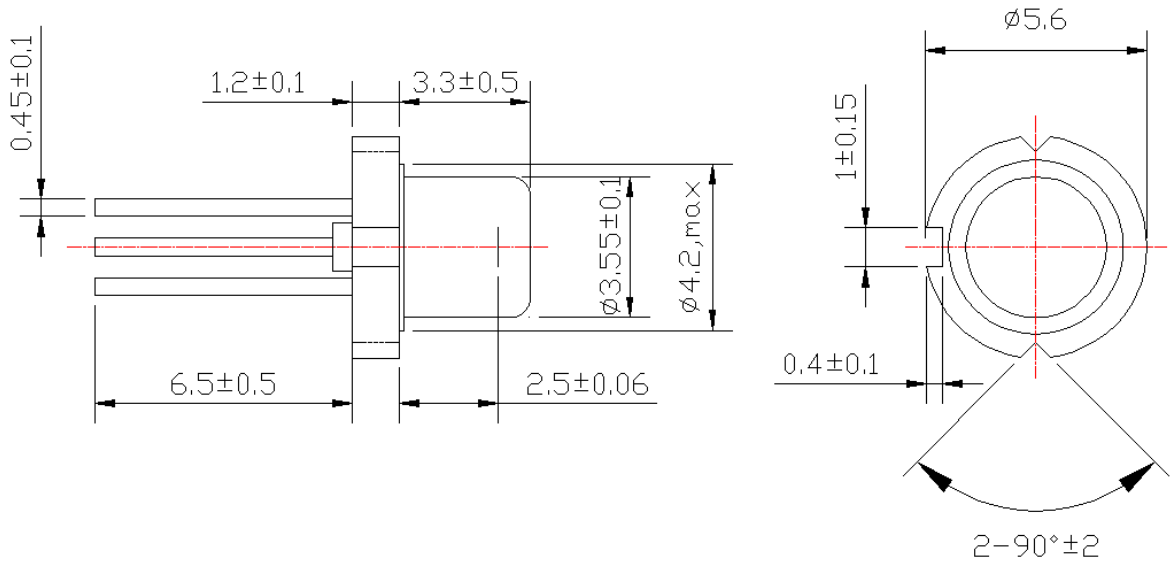
EGISMOS
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660nm RED Laser Diode

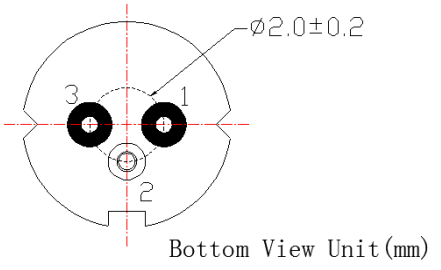
Electrical and Optical Characteristics at Tc=25℃

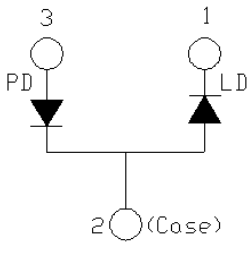
Item	Symbols	Min	Typ.	Max.	Unit	Condition
Threshold Current	I_{th}	-	45	60	mA	-
Operating Current	I_{op}	-	90	120	mA	Po=50mW
Operating Voltage	V_{op}	-	2.6	3	V	Po=50mW
Peak Wavelength	λ p	650	660	667	nm	Po=50mW
Beam Divergence (FWHM)	$\theta_{//}$	6	9	13	deg	Po=50mW
Beam Divergence (FWHM)	$\theta_{\perp}$	15	20	25	deg	Po=50mW
Monitor Current	I_m	0.01	0.25	1.0	mA	Po=50mW

Package Drawing



Electrical Connection





Specifications are subject to change without notice.

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